

**HIGH VOLTAGE POWER SCHOTTKY RECTIFIER****MBR10200C****General Description**

High voltage dual schottky rectifier suited for switch mode power supplies and other power converters. This device is intended for use in medium voltage operation, and particularly, in high frequency circuits where low switching losses and low noise are required.

MBR10200C is available in TO-220-3, TO-220-3 (2) and TO-220F-3 packages.

Features

- High Surge Capacity
- 150°C Operating Junction Temperature
- 10A Total (5A Each Diode Leg)
- Guard-ring for Stress Protection
- Pb-free Package

Applications

- Power Supply Output Rectification
- Power Management
- Instrumentation

Main Product Characteristics

$I_{F(AV)}$	2×5A
V_{RRM}	200V
T_J	150°C
$V_F(max)$	0.85V

Mechanical Characteristics

- Case: Epoxy, Molded
- Epoxy Meets UL 94V-0 @ 0.125in.
- Weight (Approximately):
1.9Grams (TO-220-3, TO-220-3 (2) and TO-220F-3)
- Finish: All External Surfaces Corrosion Resistant and Terminal
- Leads are Readily Solderable
- Lead Temperature for Soldering Purposes:
260°C Maximum for 10 Seconds

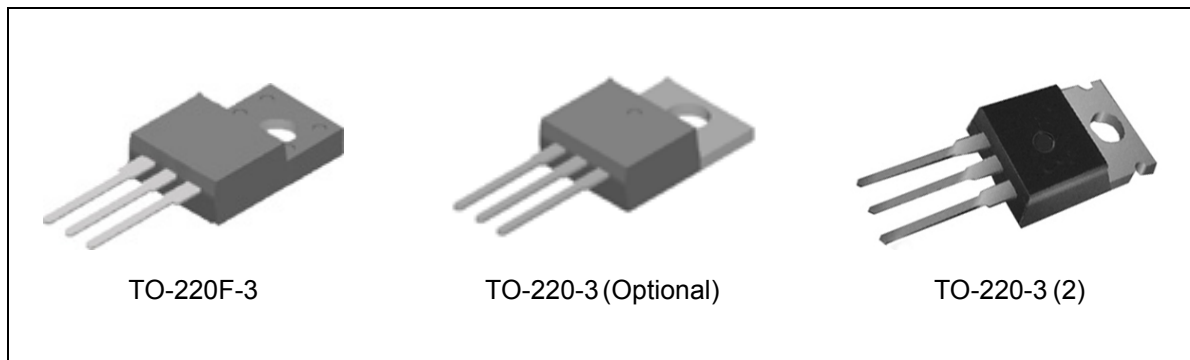


Figure 1. Package Types of MBR10200C

HIGH VOLTAGE POWER SCHOTTKY RECTIFIER **MBR10200C**

Pin Configuration

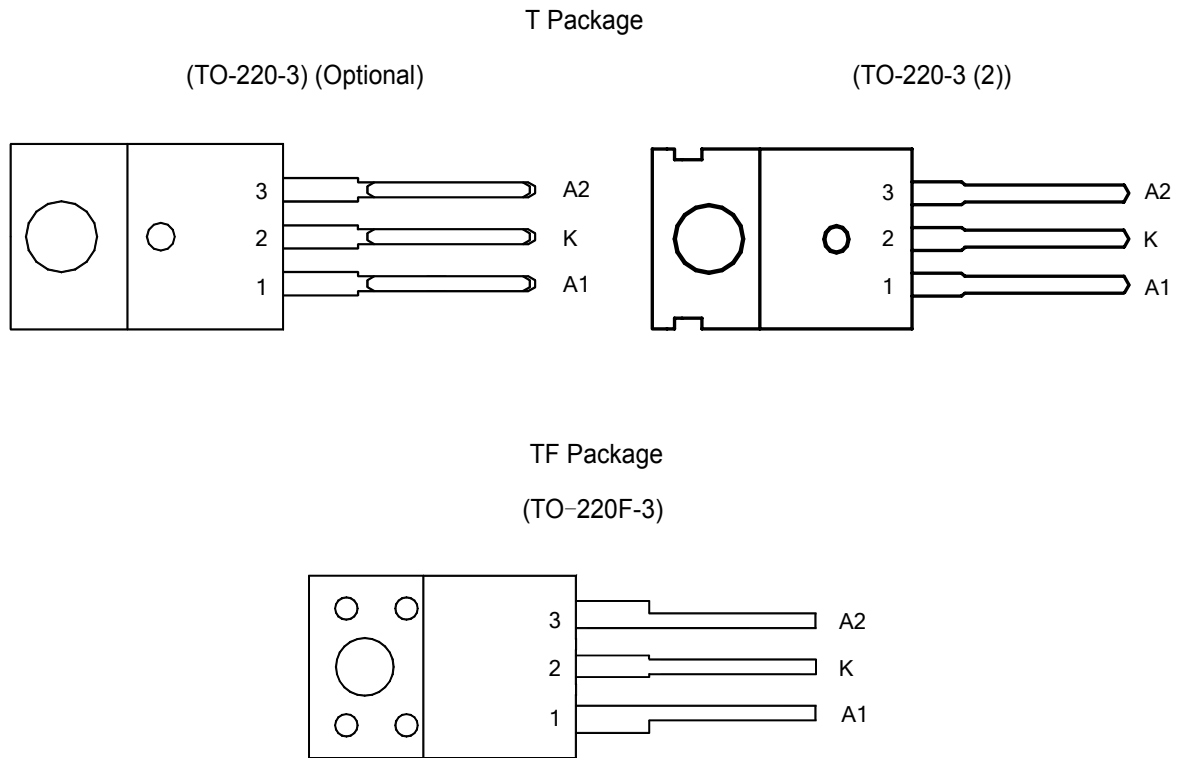


Figure 2. Pin Configuration of MBR10200C (Top View)

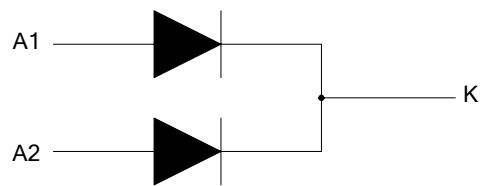


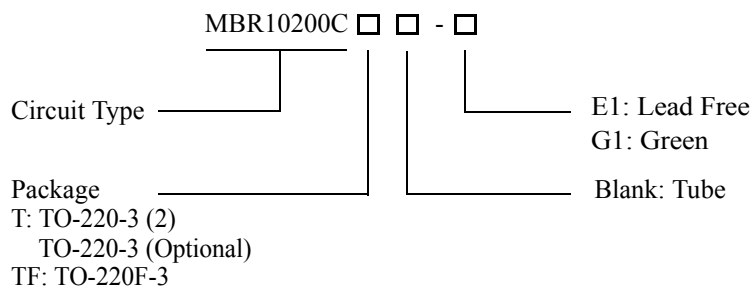
Figure 3. Internal Structure of MBR10200C



HIGH VOLTAGE POWER SCHOTTKY RECTIFIER

MBR10200C

Ordering Information



Package	Part Number		Marking ID		Packing Type
	Lead Free	Green	Lead Free	Green	
TO-220-3 (2)	MBR10200CT-E1	MBR10200CT-G1	MBR10200CT-E1	MBR10200CT-G1	Tube
TO-220F-3	MBR10200CTF-E1	MBR10200CTF-G1	MBR10200CTF-E1	MBR10200CTF-G1	Tube

BCD Semiconductor's Pb-free products, as designated with "E1" suffix in the part number, are RoHS compliant. Products with "G1" suffix are available in green packages.



HIGH VOLTAGE POWER SCHOTTKY RECTIFIER **MBR10200C**

Absolute Maximum Ratings (Each Diode Leg) (Note 1)

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	200	V
Average Rectified Forward Current (Rated V_R) $T_C=140^{\circ}C$	$I_{F(AV)}$	5	A
Peak Repetitive Forward Current (Rated V_R , Square Wave, 20kHz) $T_C=138^{\circ}C$	I_{FRM}	10	A
Non Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Half Wave, Single Phase, 60kHz)	I_{FSM}	100	A
Operating Junction Temperature (Note 2)	T_J	150	$^{\circ}C$
Storage Temperature Range	T_{STG}	-50 to 150	$^{\circ}C$
Voltage Rate of Change (Rated V_R)	dv/dt	10000	V/ μs
ESD (Machine Model=C)		>400	V
ESD (Human Body Model=3B)		>8000	V

Note 1: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to "Absolute Maximum Ratings" for extended periods may affect device reliability.

Note 2: The heat generated must be less than the thermal conductivity from Junction to Ambient: $dP_D/dT_J < 1/\theta_{JA}$.

Thermal Characteristics

Parameter	Symbol	Condition	Value	Unit	
Maximum Thermal Resistance	θ_{JC}	Junction to Case	TO-220-3/ TO-220-3 (2)	3.0	$^{\circ}C/W$
			TO-220F-3	4.5	
	θ_{JA}	Junction to Ambient	TO-220-3/ TO-220-3 (2)	60	
			TO-220F-3	60	

**HIGH VOLTAGE POWER SCHOTTKY RECTIFIER****MBR10200C****Electrical Characteristics (Each Diode Leg)**

Parameter	Condition	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage Drop (Note 3)	$I_F=5A, T_C=25^{\circ}C$	V_F	0.95	V
	$I_F=5A, T_C=125^{\circ}C$		0.85	
Maximum Instantaneous Reverse Current (Note 3)	Rated DC Voltage, $T_C=25^{\circ}C$	I_R	0.15	mA
	Rated DC Voltage, $T_C=125^{\circ}C$		15	

Note 3: Pulse Test: Pulse Width=300 μ s, Duty Cycle \leq 2.0%.



HIGH VOLTAGE POWER SCHOTTKY RECTIFIER **MBR10200C**

Typical Performance Characteristics

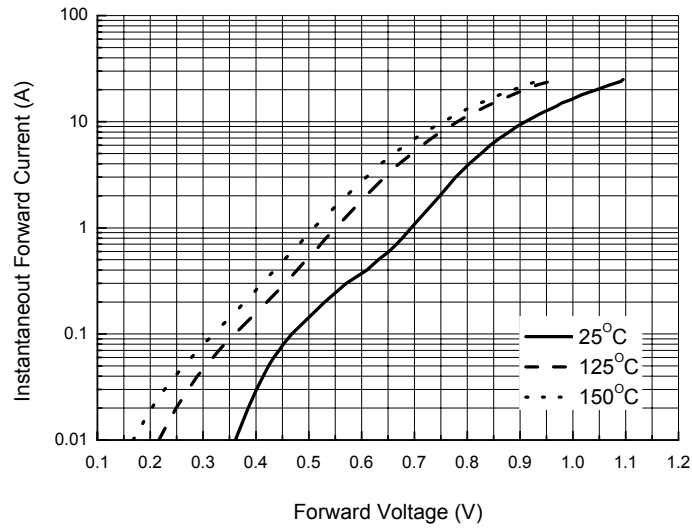


Figure 4. Typical Forward Voltage Per Diode

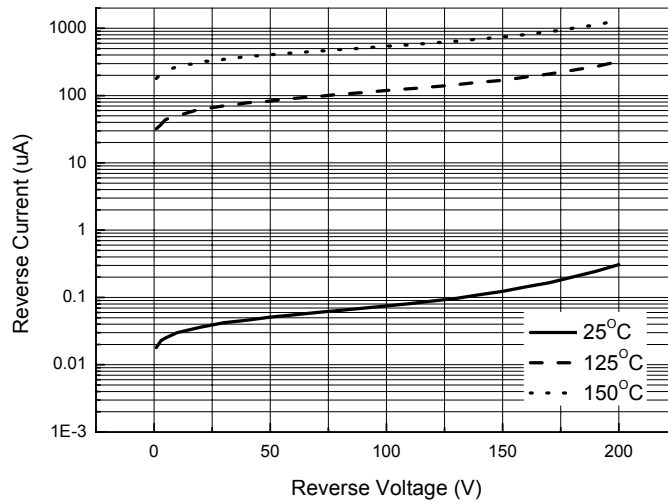


Figure 5. Typical Reverse Current Per Diode



Typical Performance Characteristics

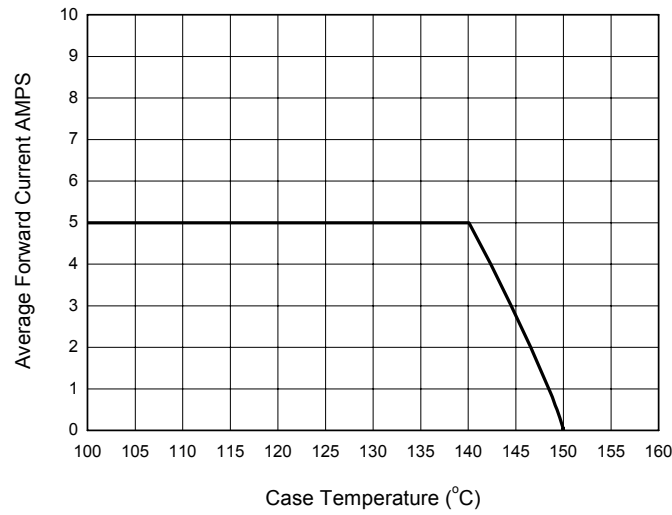


Figure 6. Average Forward Current vs. Case Temperature (Per Diode)



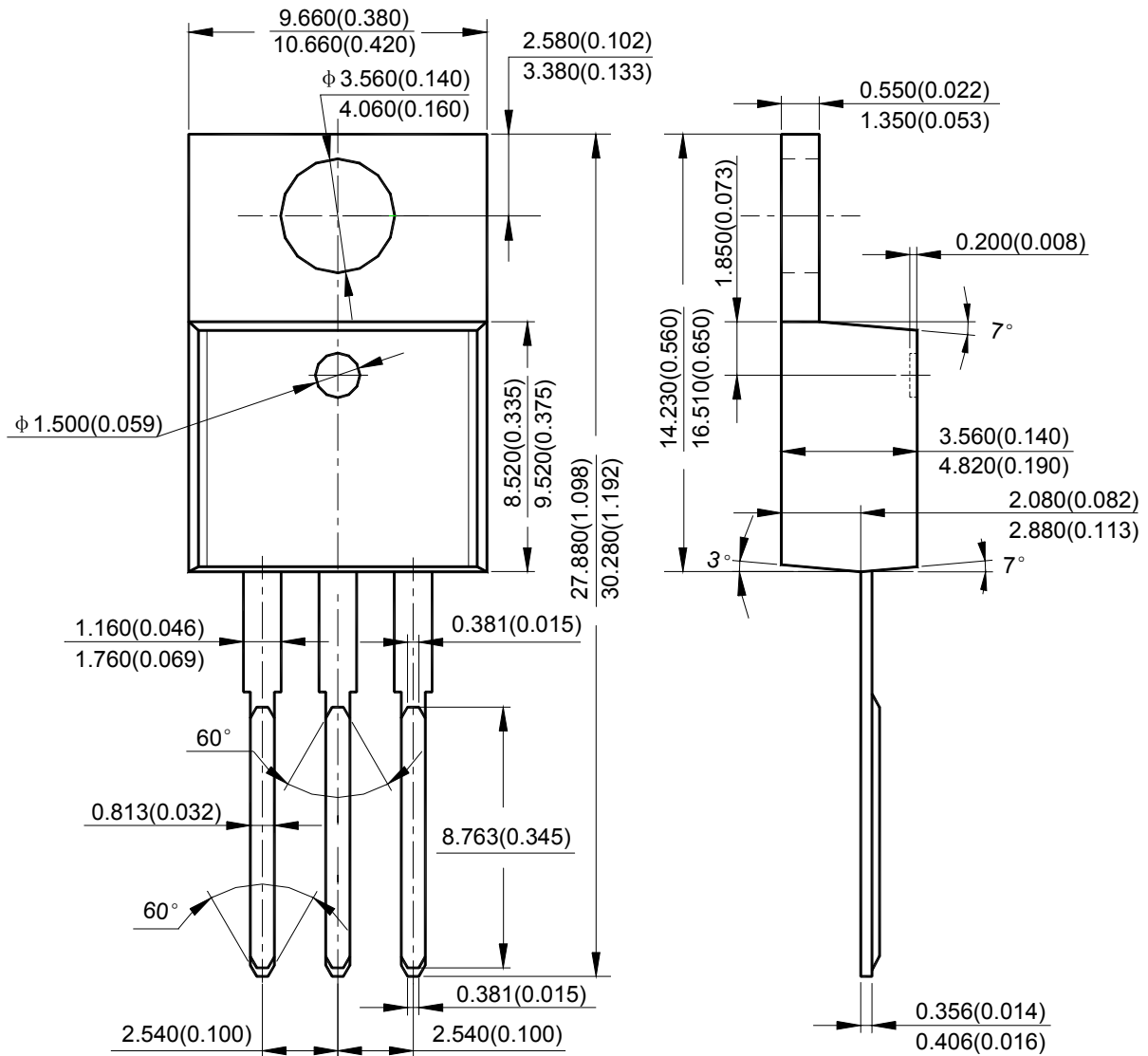
HIGH VOLTAGE POWER SCHOTTKY RECTIFIER

MBR10200C

Mechanical Dimensions

TO-220-3
(Optional)

Unit: mm(inch)





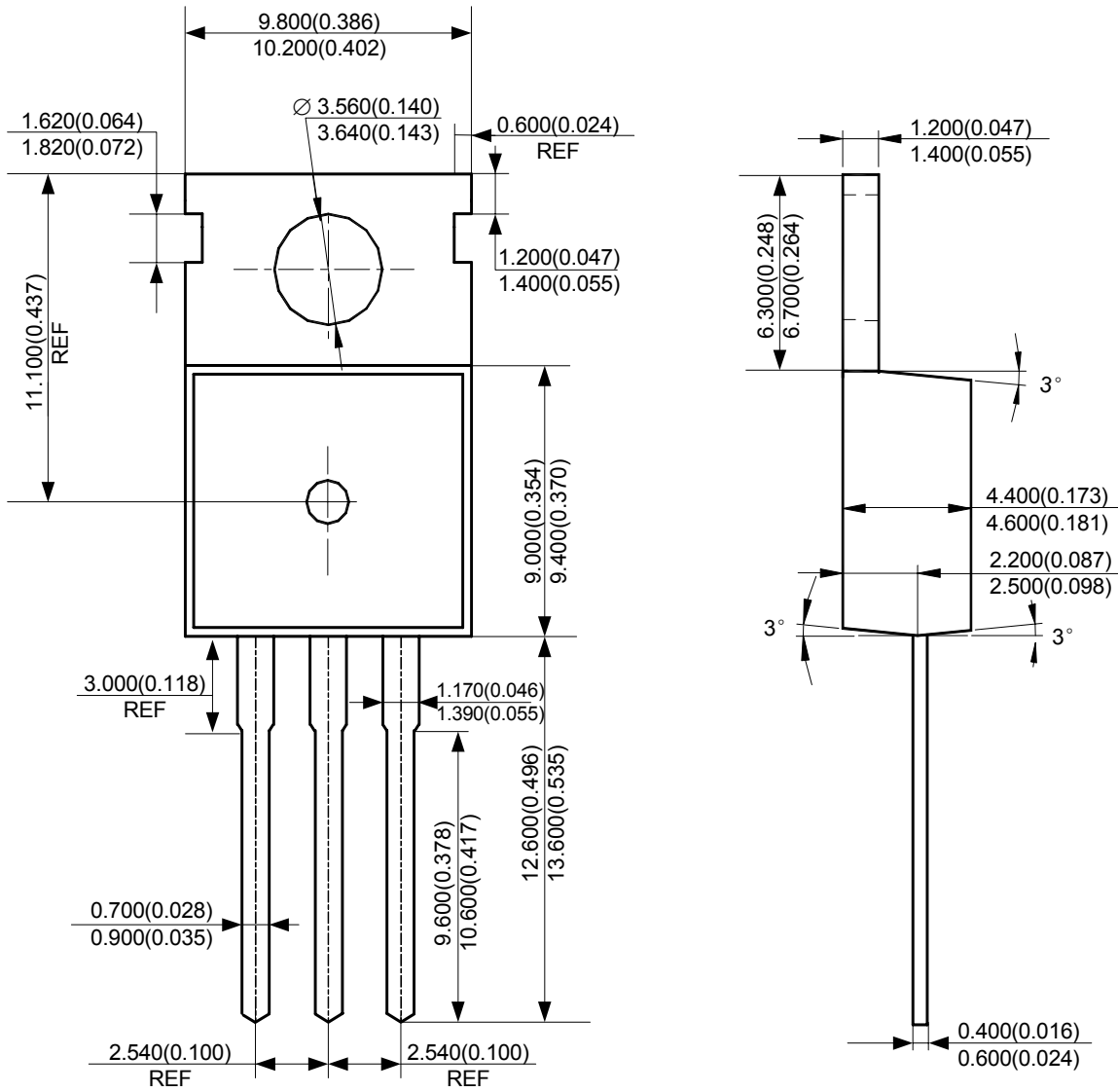
HIGH VOLTAGE POWER SCHOTTKY RECTIFIER

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Mechanical Dimensions (Continued)

TO-220-3 (2)

Unit: mm(inch)





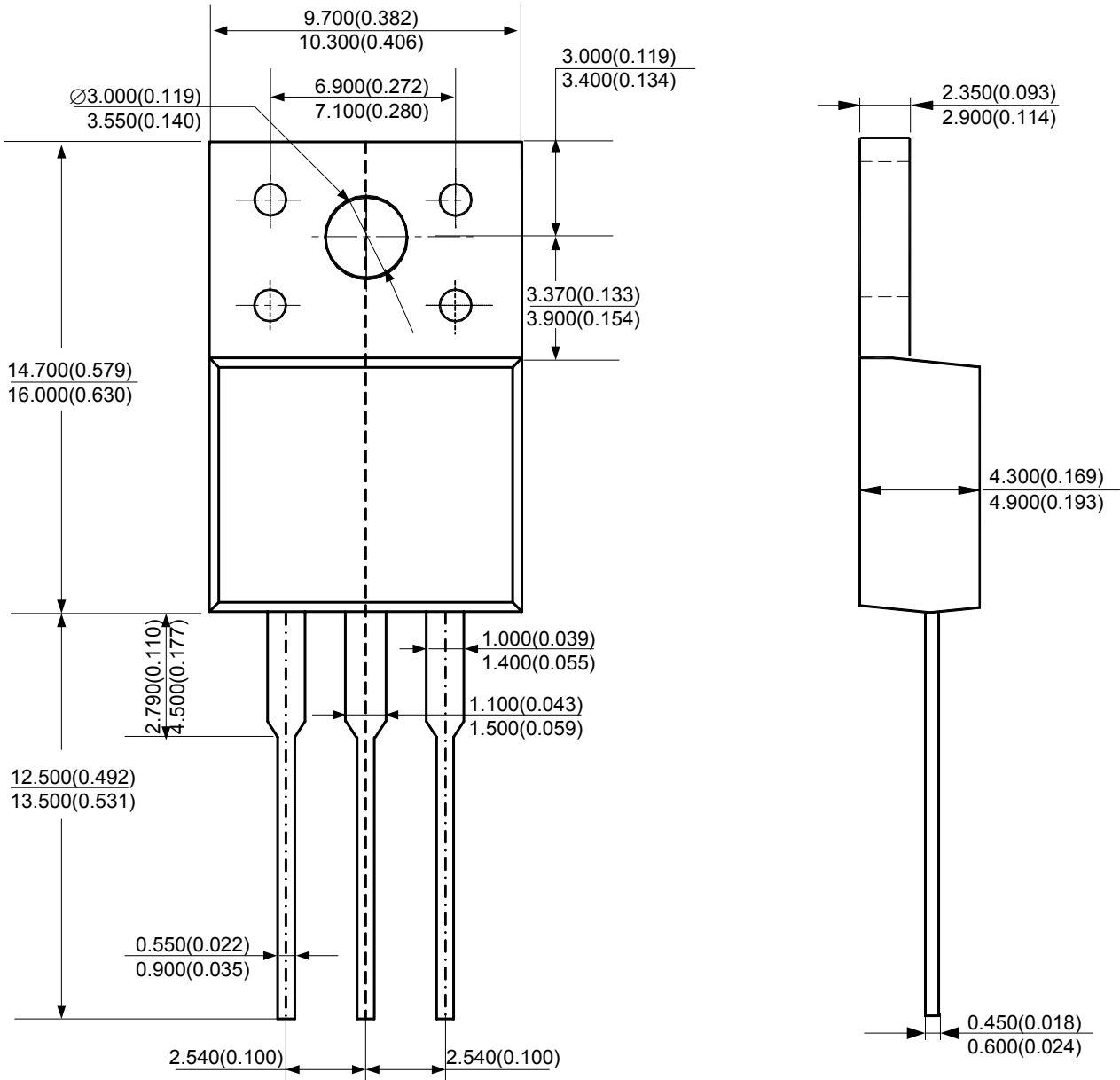
HIGH VOLTAGE POWER SCHOTTKY RECTIFIER

MBR10200C

Mechanical Dimensions (Continued)

TO-220F-3

Unit: mm(inch)





BCD Semiconductor Manufacturing Limited

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